

# PBSS306PZ

# 100 V, 4.1 A PNP low VCEsat (BISS) transistor Rev. 3 — 26 July 2011

Product data sheet

#### 1. **Product profile**

## 1.1 General description

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS306NZ.

#### 1.2 Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FF</sub>) at high I<sub>C</sub>
- High efficiency due to less heat generation
- Smaller Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

## 1.3 Applications

- High-voltage DC-to-DC conversion
- High-voltage MOSFET gate driving
- High-voltage motor control
- High-voltage power switches (e.g. motors, fans)
- Automotive applications

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-100	V
I <sub>C</sub>	collector current		-	-	-4.1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-8.2	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C = -4 \text{ A}; I_B = -400 \text{ mA}; \text{ pulsed}; $ $t_p \le 300  \mu\text{s}; \delta \le 0.02 ; T_{amb} = 25 ^{\circ}\text{C}$	-	56	80	mΩ



## 2. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		2.4
2	С	collector	4	2, 4
3	Е	emitter		1 —
4	С	collector		3
			SOT223 (SC-73)	sym028

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS306PZ	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

## 4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS306PZ	S306PZ

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

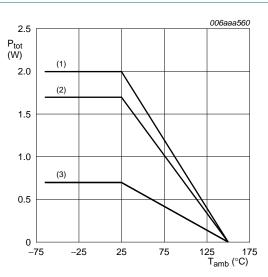
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-100	V
$V_{CEO}$	collector-emitter voltage	open base		-	-100	V
$V_{EBO}$	emitter-base voltage	open collector		-	-5	V
$I_{C}$	collector current			-	-4.1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-8.2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	<u>[1]</u>	-	0.7	W
			[2]	-	1.7	W
			[3]	-	2	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

<sup>[3]</sup> Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig 1. Power derating curves

#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resista from junction to ambient	thermal resistance	in free air	<u>[1]</u>	-	-	179	K/W
	-		[2]	-	-	74	K/W
	ambiem		[3]	-	-	63	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

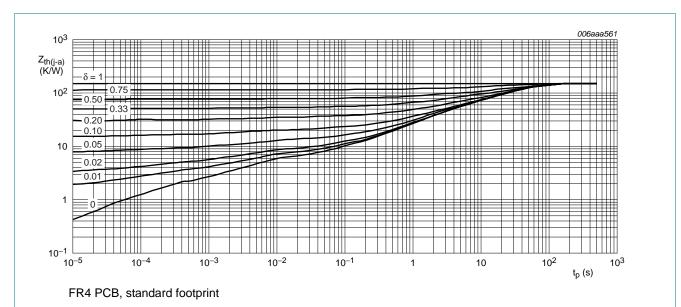


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

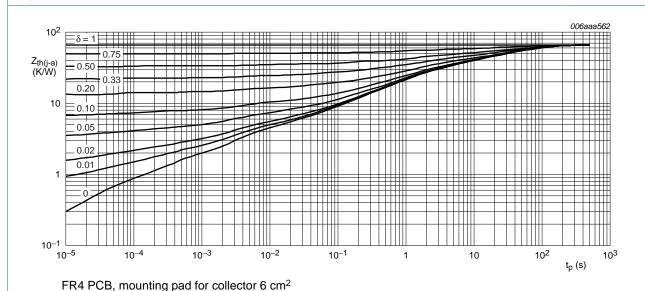
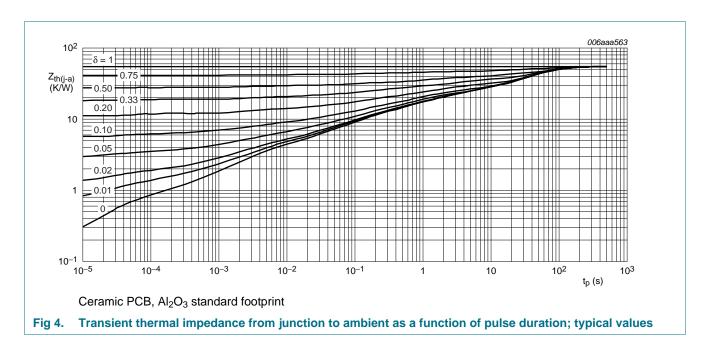


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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100 V, 4.1 A PNP low VCEsat (BISS) transistor



## 7. Characteristics

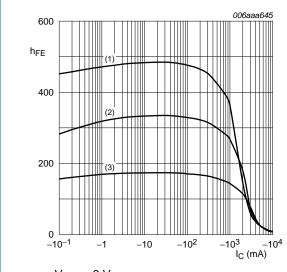
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_{CBO}$	collector-base cut-off	$V_{CB}$ = -80 V; $I_E$ = 0 A; $T_{amb}$ = 25 °C	-	-	-100	nA
	current	$V_{CB} = -80 \text{ V}; I_{E} = 0 \text{ A}; T_{j} = 150 \text{ °C};$ $T_{amb} = 25 \text{ °C}$	-	-	-50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = -48 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -2 \text{ V; } I_{C} = -0.5 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	200	300	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 \text{ °C}$	150	260	-	
		$V_{CE} = -2 \text{ V; } I_{C} = -2 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	100	175	-	
		$V_{CE} = -2 \text{ V; } I_{C} = -4 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	25	40	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = -0.5 A; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	-	-45	-65	mV
		$I_C = -1 \text{ A; } I_B = -50 \text{ mA; pulsed;}$ $t_p \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	-	-90	-130	mV
		$I_C = -4 \text{ A}$ ; $I_B = -400 \text{ mA}$ ; pulsed; $t_p \le 300 \text{ µs}$ ; $\delta \le 0.02$ ; $T_{amb} = 25 \text{ °C}$	-	-225	-320	mV
		$I_C = -4.1 \text{ A}$ ; $I_B = -410 \text{ mA}$ ; pulsed; $t_p \le 300 \text{ µs}$ ; $\delta \le 0.02$ ; $T_{amb} = 25 \text{ °C}$	-	-230	-325	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -4 A; $I_B$ = -400 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb} = 25 \ ^{\circ}C$	-	56	80	mΩ
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 Table 7.
 Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
DESat	base-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb} = 25 \ ^{\circ}C$	-	-0.81	-0.9	V
		$I_C$ = -4 A; $I_B$ = -400 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-0.93	-1.05	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-0.78	-0.85	V
t <sub>d</sub>	delay time	$V_{CC} = -12.5 \text{ V}; I_C = -3 \text{ A}; I_{Bon} = -0.15 \text{ A};$	-	15	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 0.15 A; T <sub>amb</sub> = 25 °C	-	185	-	ns
t <sub>on</sub>	turn-on time		-	200	-	ns
ts	storage time		-	150	-	ns
t <sub>f</sub>	fall time		-	175	-	ns
t <sub>off</sub>	turn-off time		-	325	-	ns
f <sub>T</sub>	transition frequency	$V_{CE} = -10 \text{ V}; I_{C} = -100 \text{ mA};$ f = 100 MHz; $T_{amb} = 25 \text{ °C}$	-	100	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	50	80	pF



 $V_{CE} = -2 V$ 

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 5. DC current gain as a function of collector current; typical values

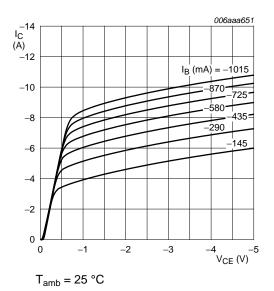
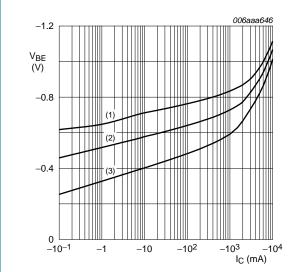


Fig 6. Collector current as a function of collector-emitter voltage; typical values



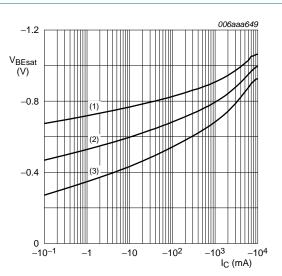
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = -55$$
 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Base-emitter voltage as a function of collector current; typical values

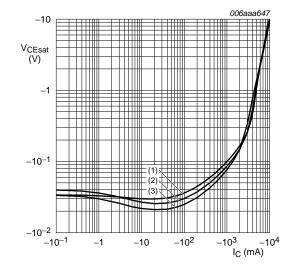


$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values



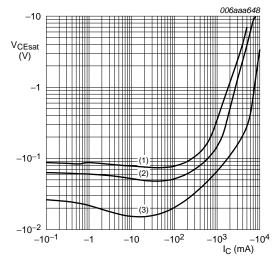
$$I_{\rm C}/I_{\rm B}=20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



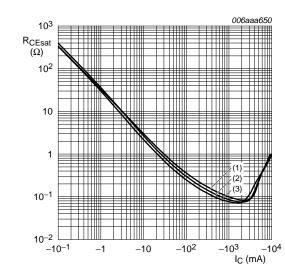
$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values



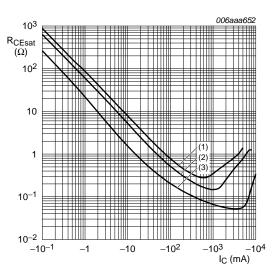
$$I_{\rm C}/I_{\rm B}=20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb} = 25$$
 °C

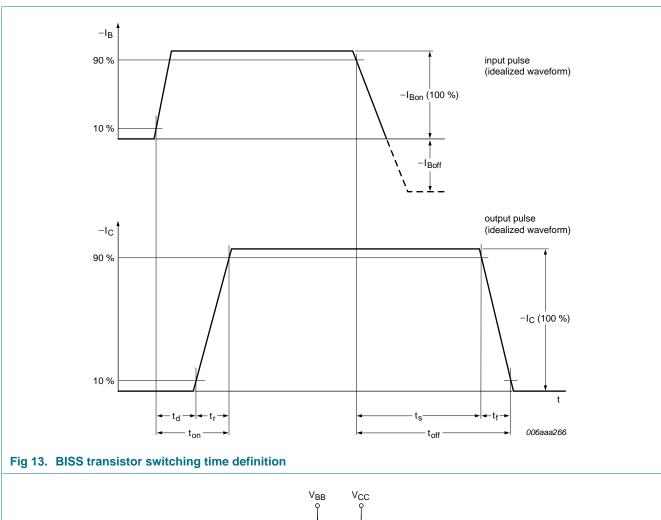
(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

## 8. Test information



 $V_{CC}$  = -12.5 V;  $I_{C}$  = -3 A;  $I_{Bon}$  = -0.15 A;  $I_{Boff}$  = 0.15 A

Fig 14. Test circuit for switching times

## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors and is suitable for use in automotive applications.

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## 9. Package outline

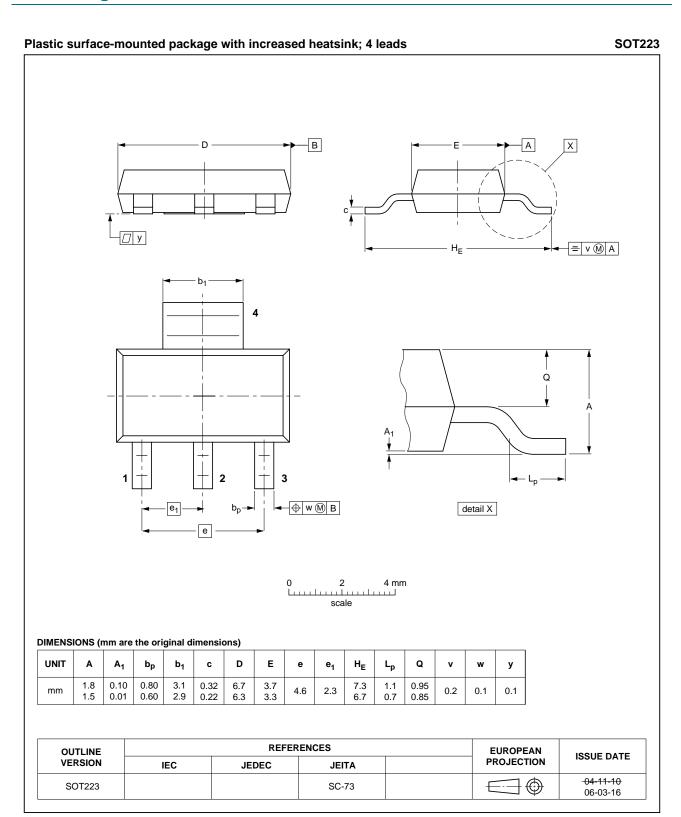
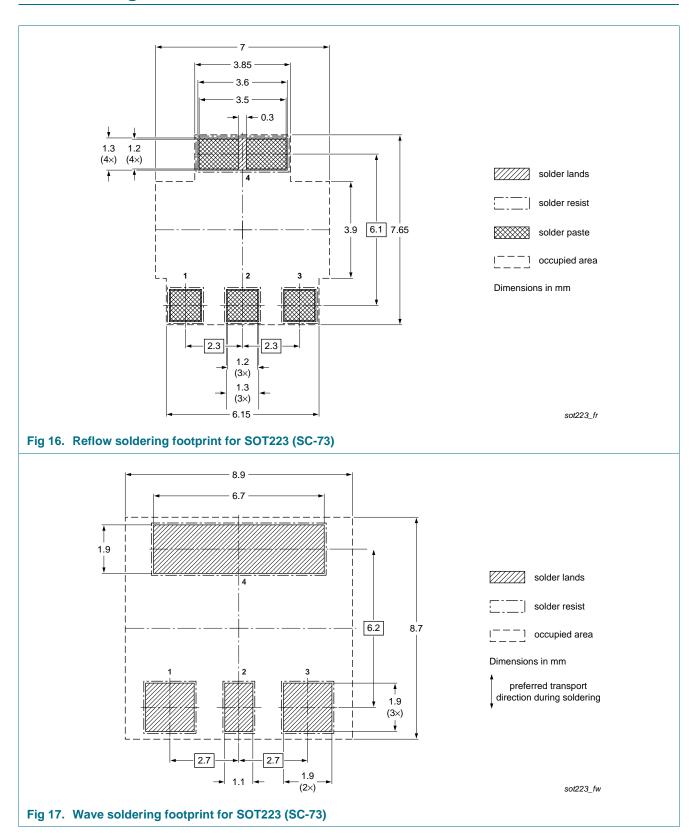


Fig 15. Package outline SOT223 (SC-73)

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## 10. Soldering



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# 11. Revision history

#### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS306PZ v.3	20110726	Product data sheet	-	PBSS306PZ v.2
Modifications:	1.2 "Features and	benefits" updated		
	<ul> <li>In 7 "Characteristic</li> </ul>	cs" new parameter added	, I <sub>CES</sub>	
	<ul> <li>Fig 15. updated</li> </ul>			
	<ul> <li>12 "Legal informat</li> </ul>	ion" updated		
PBSS306PZ v.2	20091211	Product data sheet	-	PBSS306PZ v.1
PBSS306PZ v.1	20060920	Product data sheet	-	-

## 12. Legal information

#### 12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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## 100 V, 4.1 A PNP low VCEsat (BISS) transistor

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